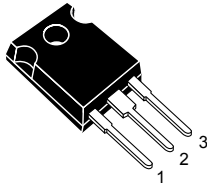
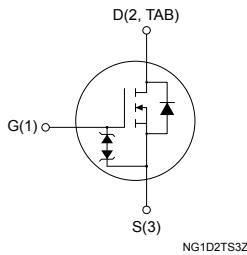


N-channel 800 V, 70 mΩ typ., 46 A MDmesh K5 Power MOSFET in a TO-247 package


TO-247

Product status link
[STW65N80K5](#)
Product summary

Product summary	
Order code	STW65N80K5
Marking	65N80K5
Package	TO-247
Packing	Tube

Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STW65N80K5	800 V	80 mΩ	46 A

- Ultra-low gate charge
- Very low FoM (figure of merit)
- Zener-protected
- 100% avalanche tested

Applications

- Switching applications

Description

This very high voltage N-channel Power MOSFET is designed using MDmesh K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	800	V
V_{GS}	Gate-source voltage	±30	V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	46	A
	Drain current (continuous) at $T_C = 100\text{ °C}$	30	
$I_{DM}^{(1)}$	Drain current (pulsed)	184	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ °C}$	446	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Operating junction temperature range		°C

1. Pulse width is limited by safe operating area.
2. $V_{DD} = 640\text{ V}$, $I_{SD} \leq 46\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DS} (\text{peak}) < V_{(BR)DSS}$.
3. $V_{DD} \leq 640\text{ V}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.28	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	50	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or non-repetitive (pulse width limited by T_J max.)	16	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	700	mJ

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified.

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	800	-	-	V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 800\text{ V}$	-	-	1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 800\text{ V}$, $T_C = 125\text{ °C}^{(1)}$	-	-	50	
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$	-	-	± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 23\text{ A}$	-	70	80	m Ω

1. Specified by design, not tested in production.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	3230	-	pF
C_{oss}	Output capacitance		-	310	-	pF
C_{rss}	Reverse transfer capacitance		-	3	-	pF
$C_{oss(eq)}^{(1)}$	Equivalent output capacitance time related	$V_{DS} = 0$ to 640 V , $V_{GS} = 0\text{ V}$	-	734	-	pF
R_g	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	1.9	-	Ω
Q_g	Total gate charge	$V_{DD} = 640\text{ V}$, $I_D = 46\text{ A}$, $V_{GS} = 0$ to 10 V (see the Figure 13. Test circuit for gate charge behavior)	-	92	-	nC
Q_{gs}	Gate-source charge		-	18	-	nC
Q_{gd}	Gate-drain charge		-	65	-	nC

1. $C_{oss(eq)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$, $I_D = 23\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	34	-	ns
t_r	Rise time		-	30	-	ns
$t_{d(off)}$	Turn-off delay time	(see the Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	90	-	ns
t_f	Fall time		-	10	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-	-	46	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-	-	184	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 46\text{ A}$	-	-	1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 46\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,	-	650	-	ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 60\text{ V}$	-	20	-	μC
I_{RRM}	Reverse recovery current	(see the Figure 14. Test circuit for inductive load switching and diode recovery times)	-	60	-	A
t_{rr}	Reverse recovery time	$I_{SD} = 46\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,	-	845	-	ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 60\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$	-	28	-	μC
I_{RRM}	Reverse recovery current	(see the Figure 14. Test circuit for inductive load switching and diode recovery times)	-	66	-	A

1. Pulse width is limited by safe operating area.
2. Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

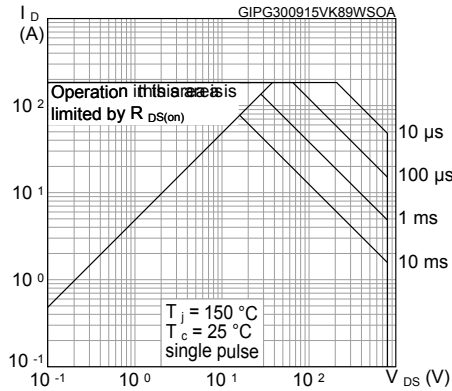


Figure 2. Normalized transient thermal impedance

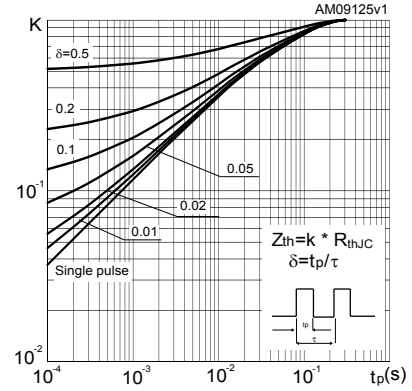


Figure 3. Typical output characteristics

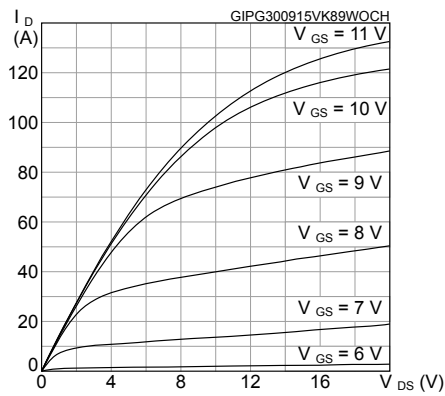


Figure 4. Typical transfer characteristics

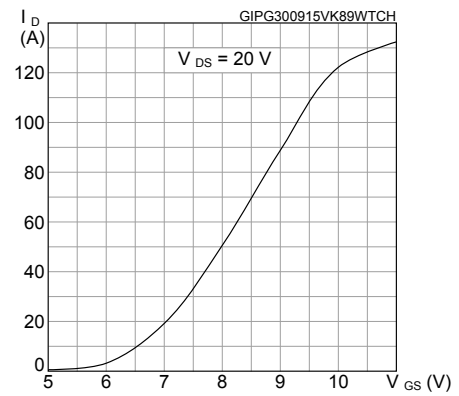


Figure 5. Typical gate charge characteristics

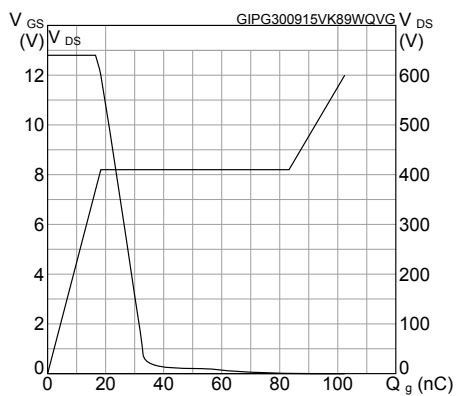


Figure 6. Typical drain-source on-resistance

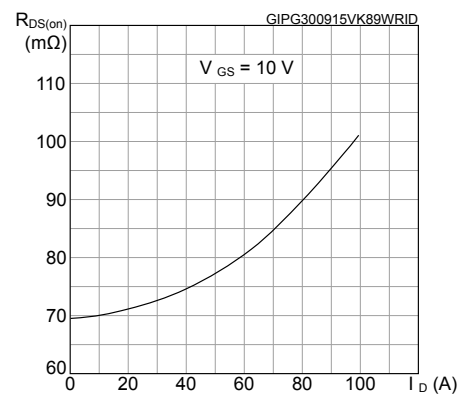


Figure 7. Typical capacitance characteristics

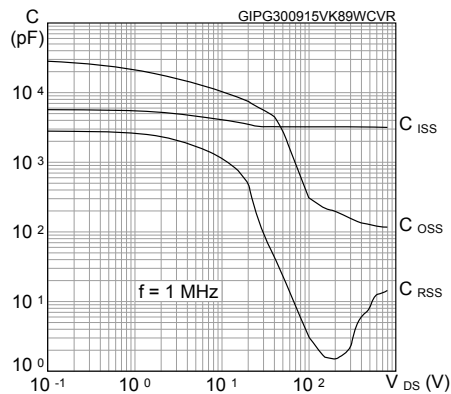


Figure 8. Normalized gate threshold vs temperature

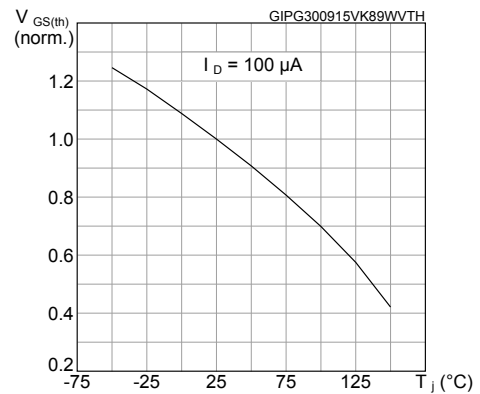


Figure 9. Normalized on-resistance vs temperature

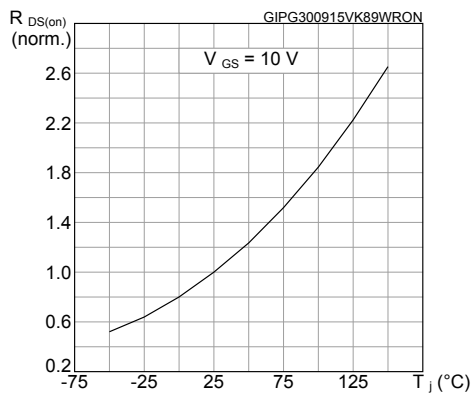


Figure 10. Normalized breakdown voltage vs temperature

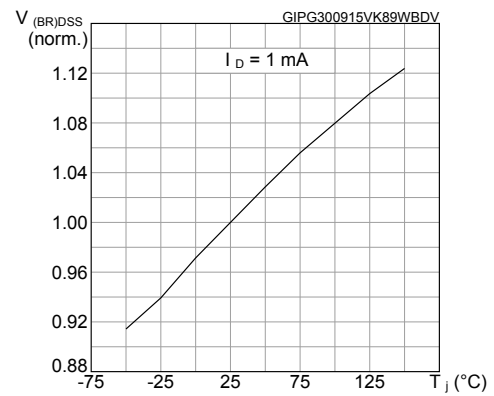
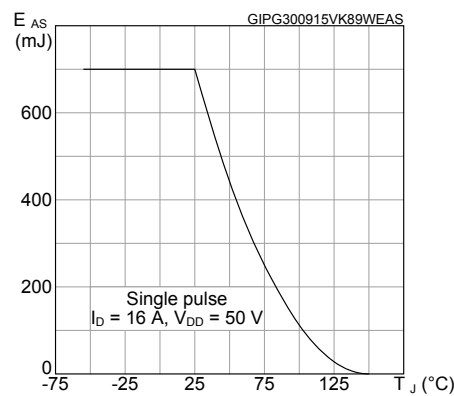


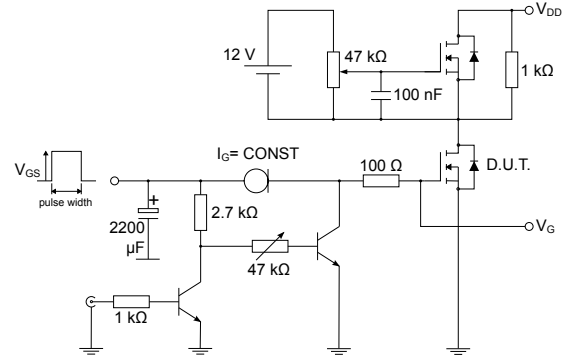
Figure 11. Maximum avalanche energy vs temperature



3 Test circuits

Figure 12. Test circuit for resistive load switching times


AM01468v1

Figure 13. Test circuit for gate charge behavior


AM01469v1

Figure 14. Test circuit for inductive load switching and diode recovery times

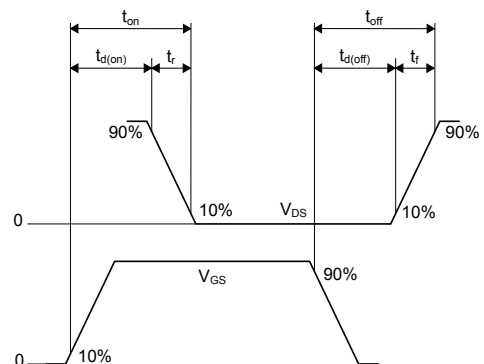

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Figure 15. Unclamped inductive load test circuit


AM01471v1

Figure 16. Unclamped inductive waveform


AM01472v1

Figure 17. Switching time waveform


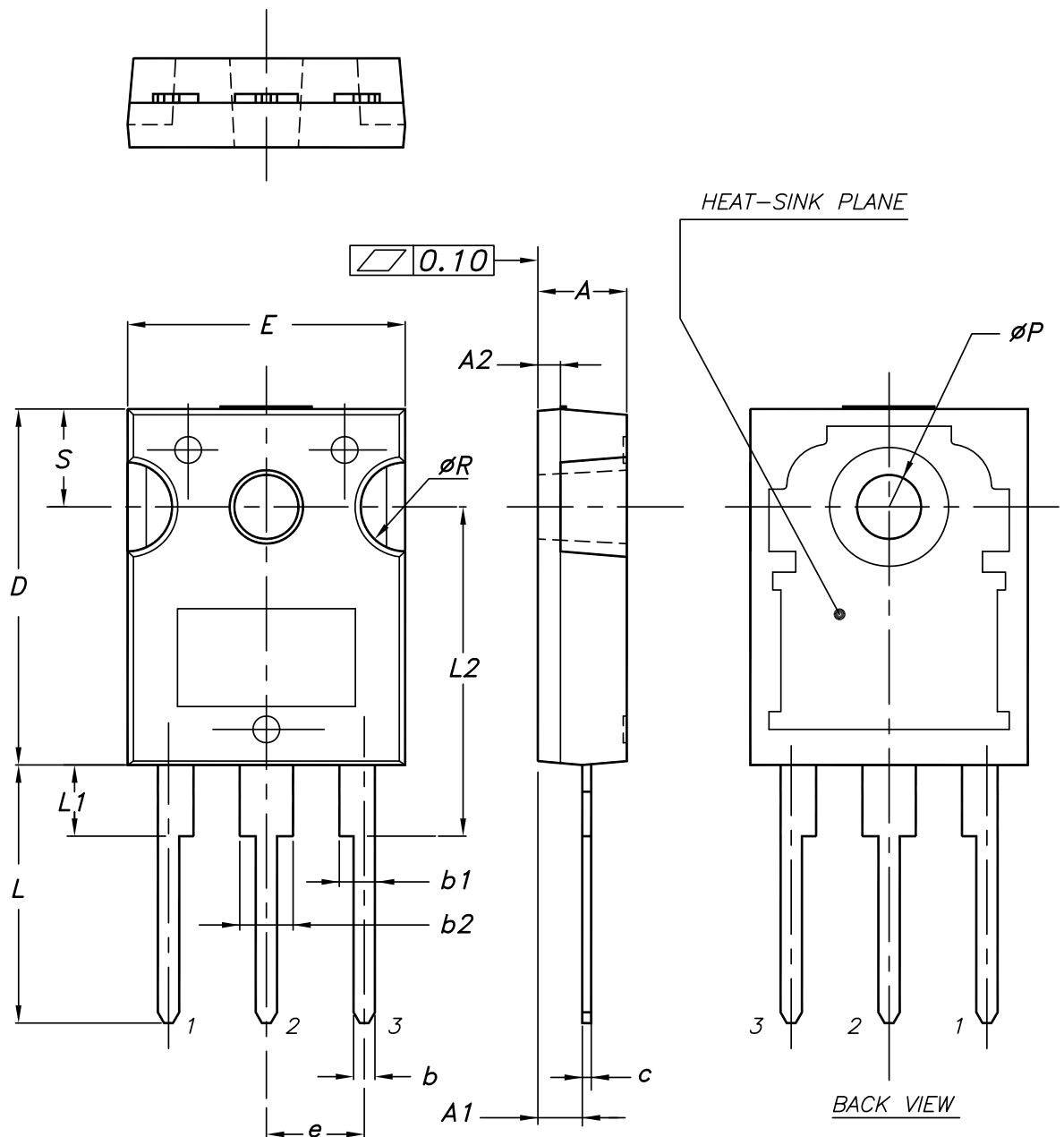
AM01473v1

4 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-247 package information

Figure 18. TO-247 package outline



0075325_11

Table 8. TO-247 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
A2		1.27	
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Revision history

Table 9. Document revision history

Date	Version	Changes
21-May-2015	1	First release.
02-Oct-2015	2	Text and formatting changes throughout document. Datasheet status promoted from preliminary to production data. On cover page: - updated title description and Features table. Updated sections - Electrical ratings and Electrical characteristics. Added section - Electrical characteristics (curves).
03-Dec-2025	3	Updated Section 4: Package information . Minor text changes.



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